XP134A1275SR

TOREX

Power MOS FET

- ◆P-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance : 0.075Ω (max)
- ◆Ultra High-Speed Switching
- ◆SOP-8 Package
- ◆2 FET Devices Built-in

■General Description

The XP134A1275SR is a P-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.
Two FET devices are built-into the one package.
Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.
The small SOP-8 package makes high density mounting possible.

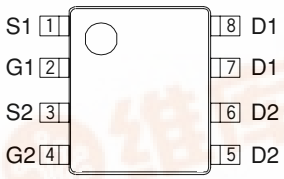
■Applications

- ●Notebook PCs
- ●Cellular and portable phones
- ●On-board power supplies
- ●Li-ion battery systems

■Features

Low on-state resistance : Rds (on) = 0.075Ω (Vgs = -4.5V)
: Rds (on) = 0.115Ω (Vgs = -2.5V)
Ultra high-speed switching
Operational Voltage : -2.5V
High density mounting : SOP-8

■Pin Configuration

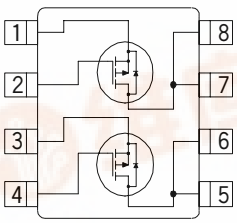


SOP-8
(TOP VIEW)

■Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1	S1	Source
2	G1	Gate
3	S2	Source
4	G2	Gate
5~6	D2	Drain
7~8	D1	Drain

■Equivalent Circuit



P-Channel MOS FET
(2 devices built-in)

■Absolute Maximum Ratings

Ta=25°C

PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	Vdss	- 20	V
Gate - Source Voltage	Vgss	±12	V
Drain Current (DC)	Id	- 4.5	A
Drain Current (Pulse)	Idp	- 18	A
Reverse Drain Current	Idr	- 4.5	A
Continuous Channel Power Dissipation (note)	Pd	2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	- 55 ~ 150	°C

(note) : When implemented on a glass epoxy PCB

■Electrical Characteristics

DC Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds = - 20V , Vgs = 0V			- 10	μA
Gate-Source Leakage Current	Igss	Vgs = ±12V , Vds = 0V			±1	μA
Gate-Source Cut-off Voltage	Vgs (off)	Id = -1mA , Vds = - 10V	- 0.5		- 1.2	V
Drain-Source On-state Resistance (note)	Rds (on)	Id = - 2.5A , Vgs = - 4.5V		0.062	0.075	Ω
		Id = - 2.5A , Vgs = - 2.5V		0.095	0.115	Ω
Forward Transfer Admittance (note)	| Yfs |	Id = - 2.5A , Vds = - 10V		7.5		S
Body Drain Diode Forward Voltage	Vf	If = - 4.5A , Vgs = 0V		- 0.85	- 1.1	V

(note) : Effective during pulse test.

Dynamic Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds = - 10V , Vgs = 0V f = 1 MHz		770		pF
Output Capacitance	Coss			440		pF
Feedback Capacitance	Crss			190		pF

Switching Characteristics

Ta=25°C

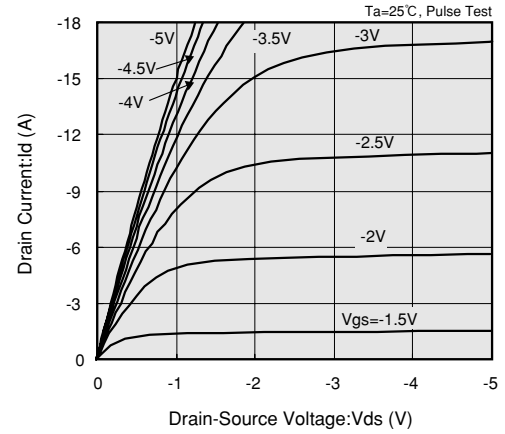
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs = - 5V , Id = - 2.5A Vdd = - 10V		15		ns
Rise Time	tr			20		ns
Turn-off Delay Time	td (off)			55		ns
Fall Time	tf			30		ns

Thermal Characteristics

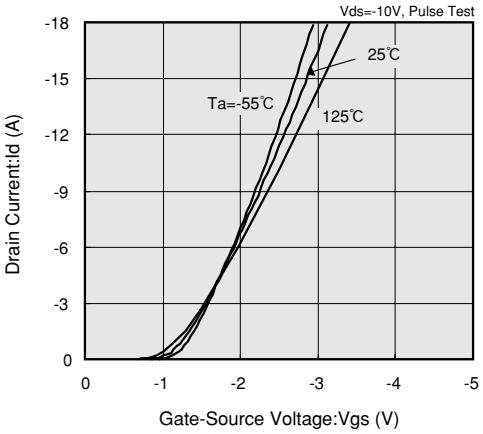
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB		62.5		°C / W

■Typical Performance Characteristics

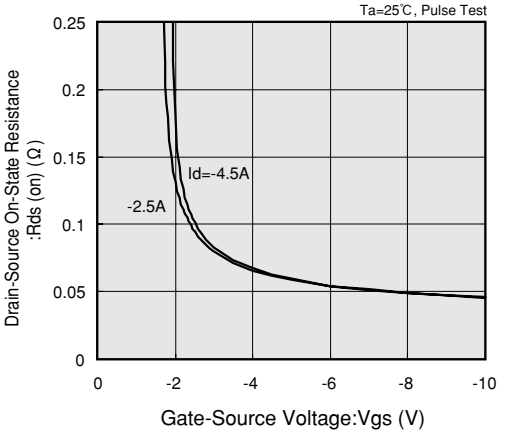
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



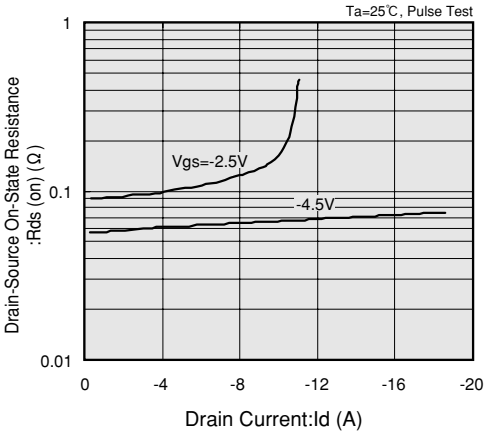
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



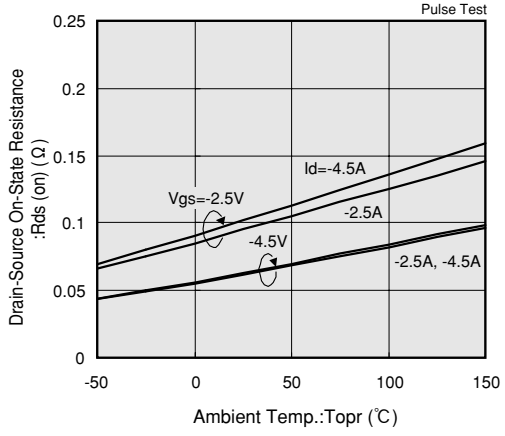
DRAIN-SOURCE ON-STATE RESISTANCE
vs. GATE-SOURCE VOLTAGE



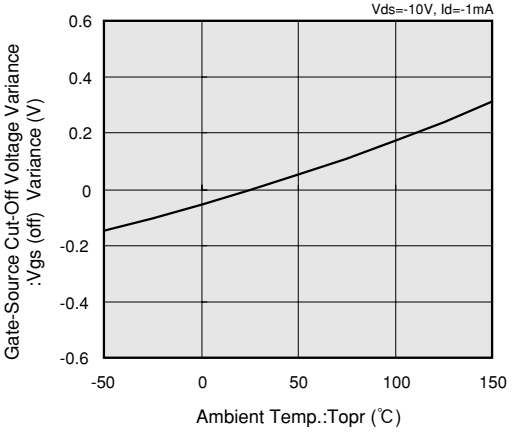
DRAIN-SOURCE ON-STATE RESISTANCE
vs. DRAIN CURRENT



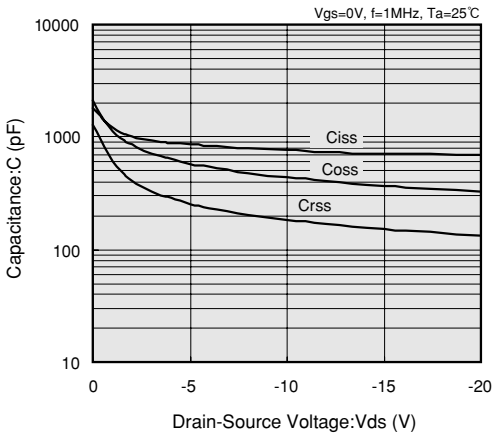
DRAIN-SOURCE ON-STATE RESISTANCE
vs. AMBIENT TEMPERATURE



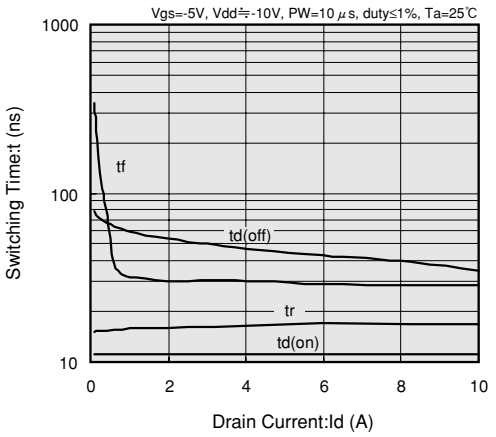
GATE-SOURCE CUT-OFF VOLTAGE VARIANCE
vs. AMBIENT TEMPERATURE



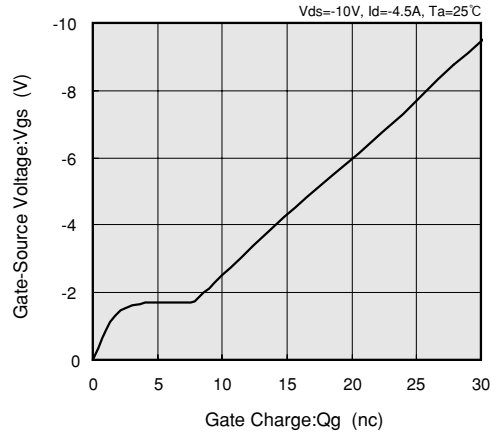
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



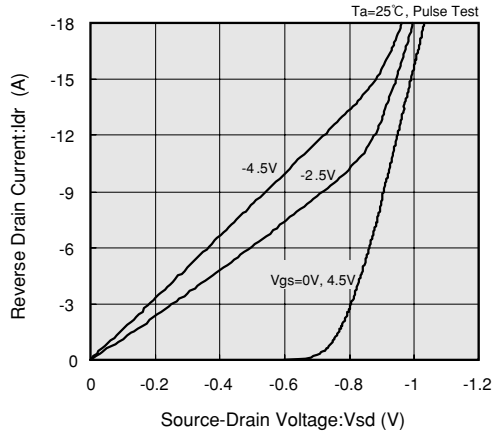
SWITCHING TIME vs. DRAIN CURRENT



GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT
vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH